



8N65-E

Preliminary

Power MOSFET

**8A, 650V N-CHANNEL
POWER MOSFET**

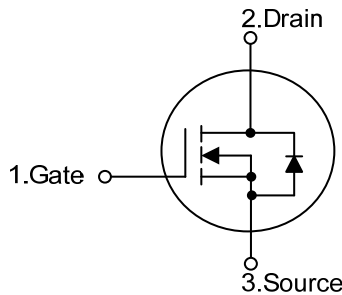
■ DESCRIPTION

The UTC **8N65-E** is a high voltage and high current power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications at power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- * $R_{DS(ON)} < 1.4 \Omega @ V_{GS} = 10 V, I_D = 4 A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

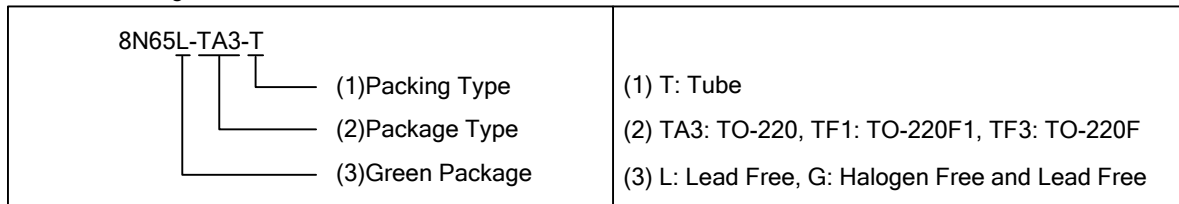
■ SYMBOL



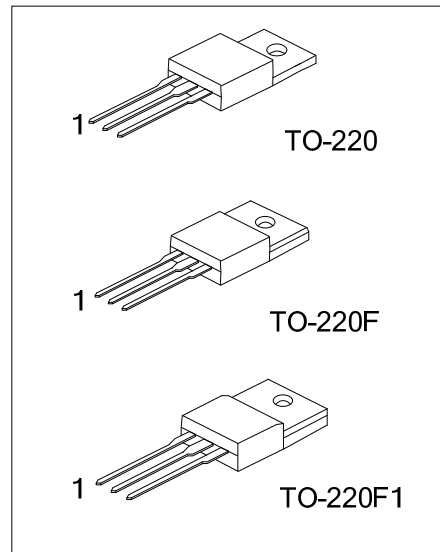
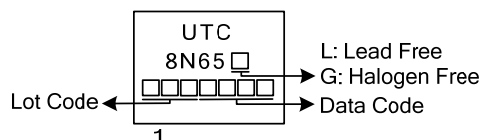
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N65L-TA3-T	8N65G-TA3-T	TO-220	G	D	S	Tube
8N65L-TF3-T	8N65G-TF3-T	TO-220F	G	D	S	Tube
8N65L-TF1-T	8N65G-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	225	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.8	V/ns
Power Dissipation	TO-220	P_D	147	W
	TO-220F/TO-220F1		48	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L=7\text{mH}$, $I_{AS}=8\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD}\leq 8\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

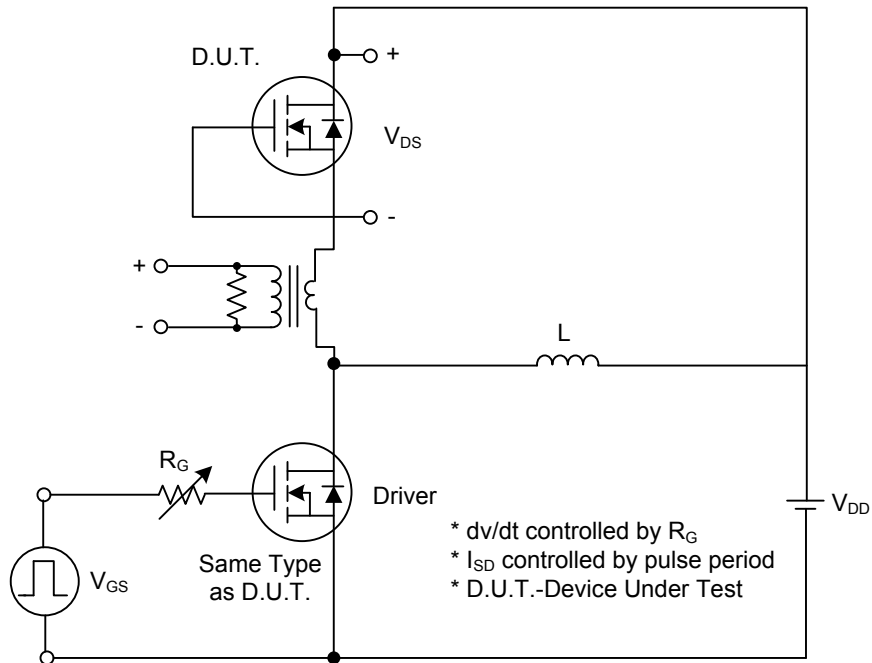
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.85	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.6	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

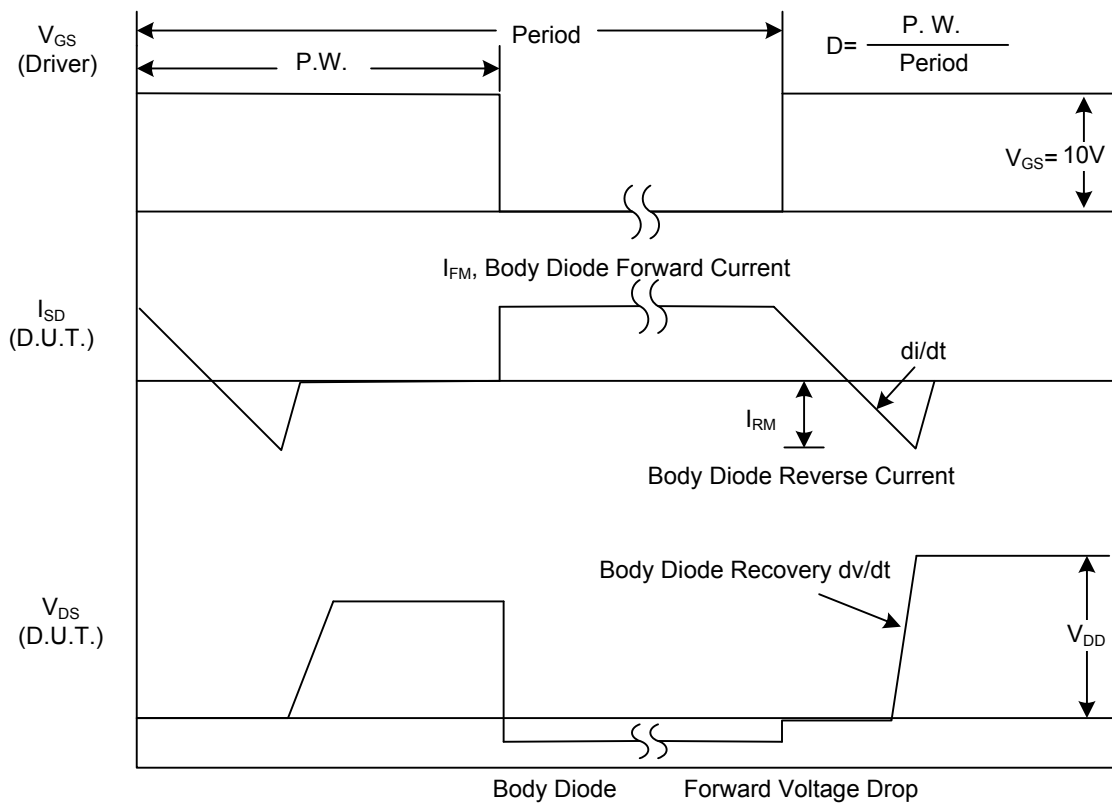
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
					Reverse	-100
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		0.7		$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 4\text{ A}$			1.4	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		331		pF
Output Capacitance	C_{OSS}			90		pF
Reverse Transfer Capacitance	C_{RSS}			8		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 1.3\text{ A}$ $I_G = 100\ \mu\text{A}$ (Note 1, 2)		23		nC
Gate-Source Charge	Q_{GS}			7.5		nC
Gate-Drain Charge	Q_{GD}			4		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 0.5\text{ A},$ $R_G = 25\ \Omega$ (Note 1, 2)		63		ns
Turn-On Rise Time	t_R			31		ns
Turn-Off Delay Time	$t_{D(OFF)}$			155		ns
Turn-Off Fall Time	t_F			36		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				8	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				32	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 8\text{ A}$			1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0\text{ V}, I_S = 8\text{ A},$		356		ns
Reverse Recovery Charge	Q_{RR}	$di_F/dt = 100\text{ A}/\mu\text{s}$		3.9		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

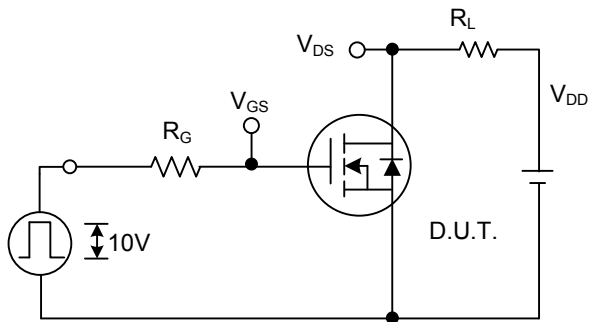


Peak Diode Recovery dv/dt Test Circuit

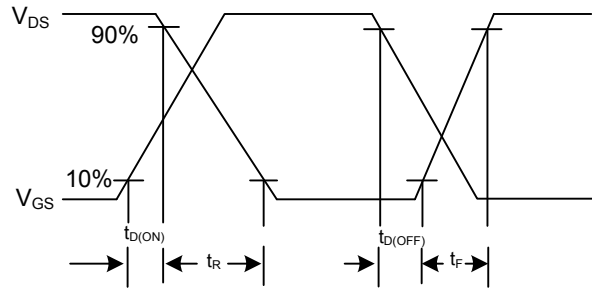


Peak Diode Recovery dv/dt Waveforms

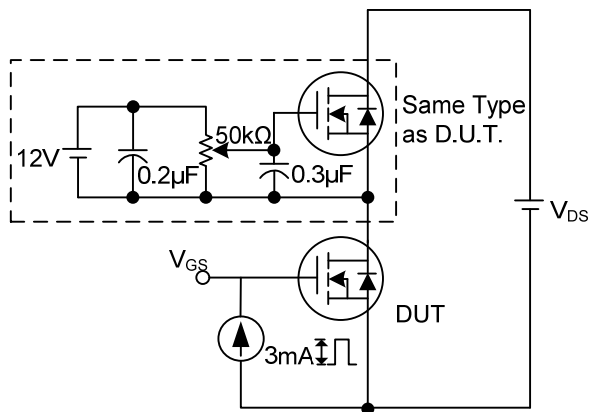
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



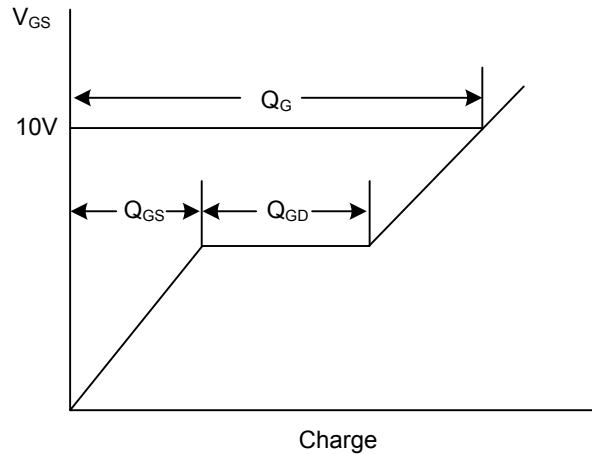
Switching Test Circuit



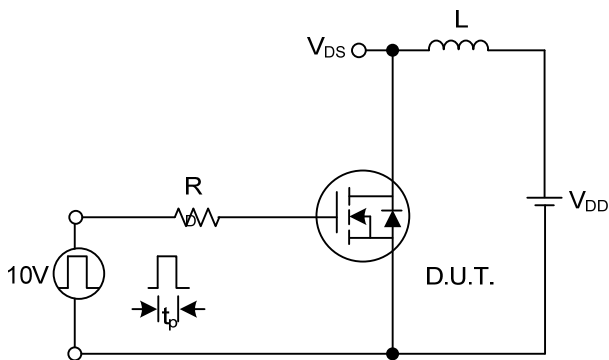
Switching Waveforms



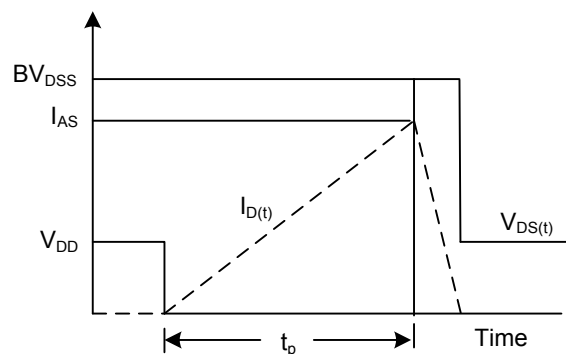
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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